

Features

- Advanced trench technology
- Low on-resistance
- Low gate charge
- HBM: JESD22-A114-B: 1B

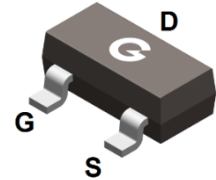
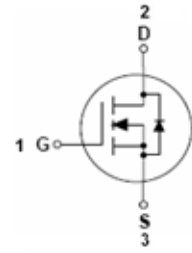
HF

APPLICATIONS

- Power switching application
- DC-DC converters

Mechanical Data

- Case: SOT-23-3L
- Molding Compound: UL Flammability Classification Rating 94V-0
- Terminals: Matte tin-plated leads; solderability-per MIL-STD-202, Method 208



SOT-23-3L

Ordering Information

Part Number	Package	Shipping Quantity	Marking Code
BL450N06-3L	SOT-23-3L	3000 pcs / Tape & Reel	450N06

Maximum Ratings (@ T_A = 25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V _{DSS}	60	V
Gate-to-Source Voltage	V _{GSS}	±20	V
Continuous Drain Current (T _A = 25°C) *1	I _D	4.1	A
Continuous Drain Current (T _A = 70°C) *1		3.3	A
Pulsed Drain Current (t _p = 10μs, T _A = 25°C)	I _{DM}	41	A
Single Pulse Avalanche Energy *3	E _{AS}	15	mJ
Power Dissipation (T _A = 25°C) *1	P _D	1.5	W
Operating Junction Temperature Range	T _J	-55 ~ +150	°C
Storage Temperature Range	T _{STG}	-55 ~ +150	°C

Thermal Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal Resistance Junction-to-Case	R _{θJC}	-	28	32	°C/W
Thermal Resistance Junction-to-Air *1	R _{θJA}	-	75	83	°C/W

Electrical Characteristics (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
V _{DS}	Drain-Source Breakdown Voltage	V _{GS} = 0V, I _D = 250μA	60	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 48V, V _{GS} = 0V	-	-	1	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} = ±20V, V _{DS} = 0V	-	-	±100	nA
On Characteristics						
R _{DS(ON)}	Drain-Source On-resistance ^{*2}	V _{GS} = 10V, I _D = 4A	-	39	45	mΩ
		V _{GS} = 4.5V, I _D = 3A	-	43	50	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250μA	1	1.7	2.5	V
R _G	Gate Resistance	V _{GS} = 0V, f = 1MHz	-	1.8	-	Ω
Dynamic Characteristics						
C _{ISS}	Input Capacitance	V _{GS} = 0V	-	945	-	pF
C _{OSS}	Output Capacitance	V _{DS} = 30V	-	44	-	
C _{RSS}	Reverse Transfer Capacitance	f = 1.0MHz	-	32	-	
Switching Characteristics						
t _{d(ON)}	Turn-on Delay Time ^{*4}	V _{DD} = 30V	-	8	-	ns
t _r	Turn-on Rise Time ^{*4}	V _{GS} = 10V	-	4	-	
t _{d(OFF)}	Turn-Off Delay Time ^{*4}	R _G = 3Ω	-	32	-	
t _f	Turn-Off Fall Time ^{*4}	R _L = 7.5Ω	-	7	-	
Q _G	Total Gate-Charge	V _{DD} = 48V	-	20.4	-	nC
Q _{GS}	Gate to Source Charge	V _{GS} = 10V	-	3	-	
Q _{GD}	Gate to Drain (Miller) Charge	I _D = 3A	-	3.3	-	
Source-Drain Diode Characteristics						
V _{SD}	Diode Forward Voltage ^{*2}	I _{SD} = 5A, V _{GS} = 0V	-	0.8	1.2	V
t _{rr}	Reverse Recovery Time	I _{SD} = 3A, V _{GS} = 0V	-	17	-	ns
Q _{rr}	Reverse Recovery Charge	dI/dt = 100A/μs	-	9	-	nC

Notes:

- The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper
- The data tested by pulsed, pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- The E_{AS} data shows Max. rating. The test condition is $V_{DD} = 30V, V_{GS} = 10V, L = 0.5mH$
- Guaranteed by design, not subject to production

Ratings and Characteristics Curves (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

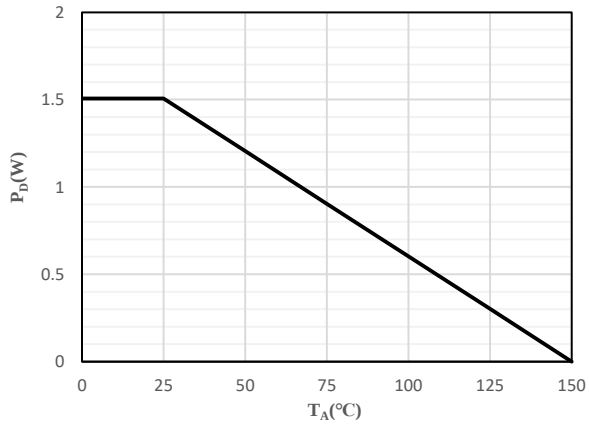


Fig 1 Power Dissipation

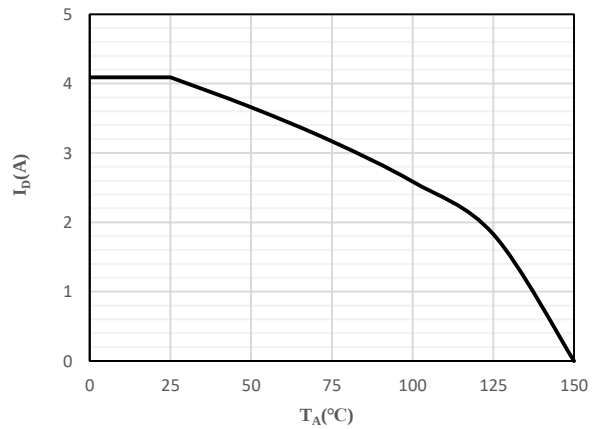


Fig 2 Drain Current

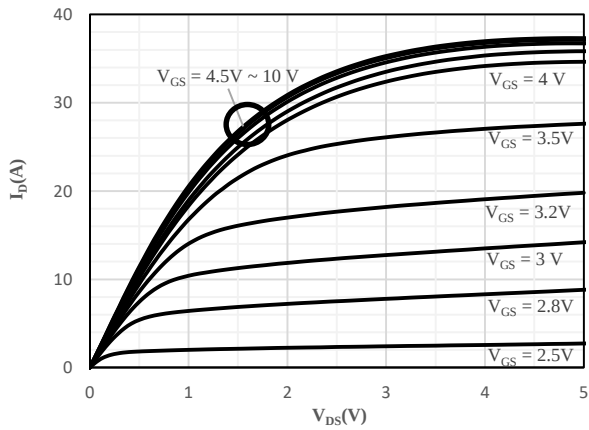


Fig 3 Typical Output Characteristics

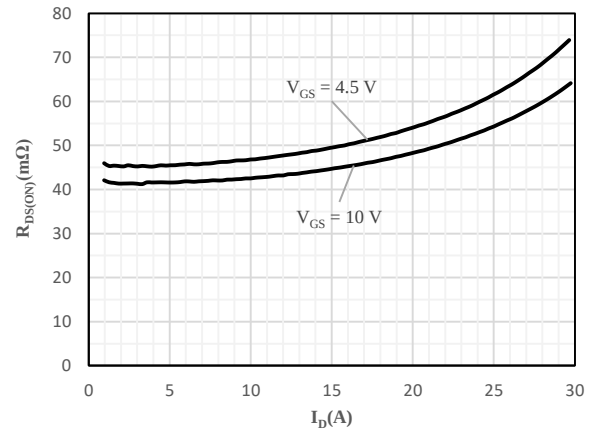


Fig 4 On-Resistance vs. Drain Current
and Gate Voltage

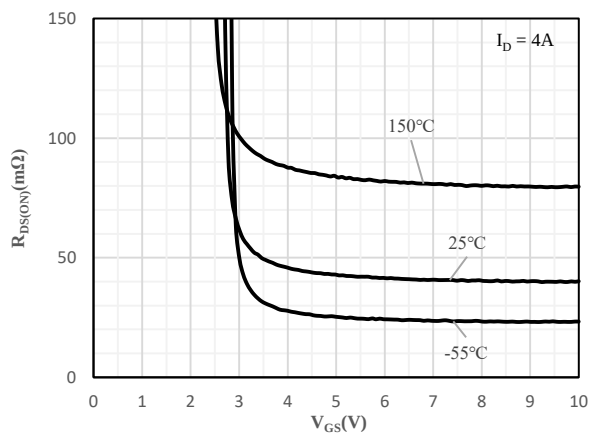


Fig 5 On-Resistance vs. Gate-Source Voltage

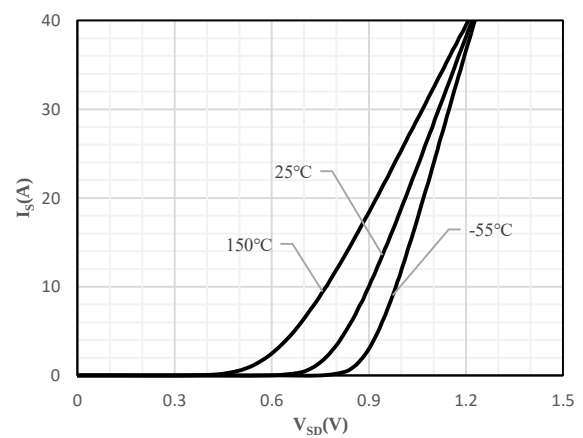


Fig 6 Body-Diode Characteristics

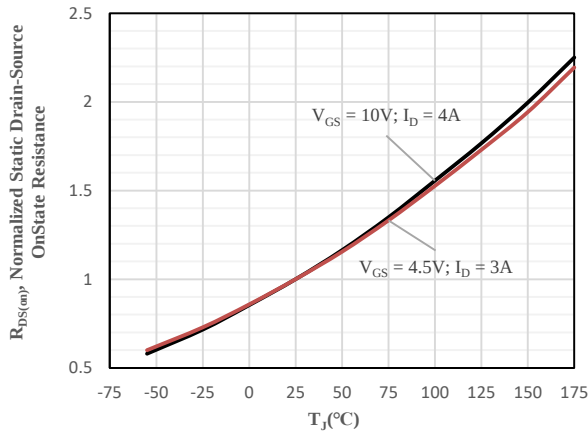


Fig 7 Normalized On-Resistance vs. Junction Temperature

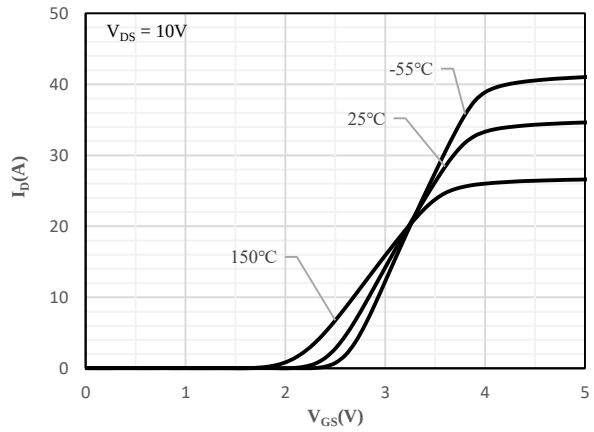


Fig 8 Transfer Characteristics

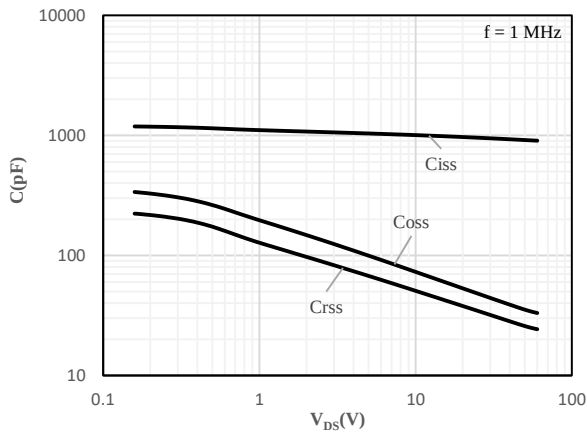


Fig 9 Capacitance Characteristics

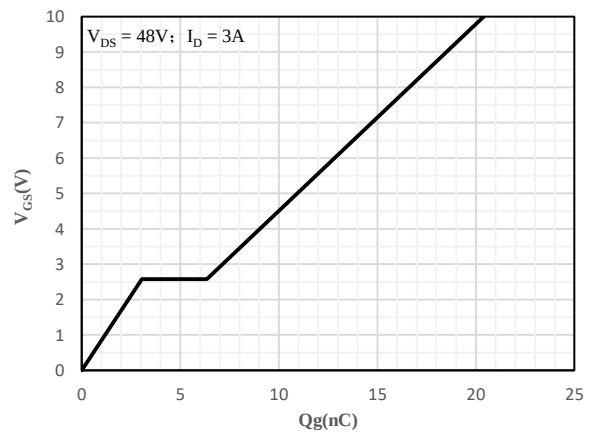


Fig 10 Gate-Charge Characteristics

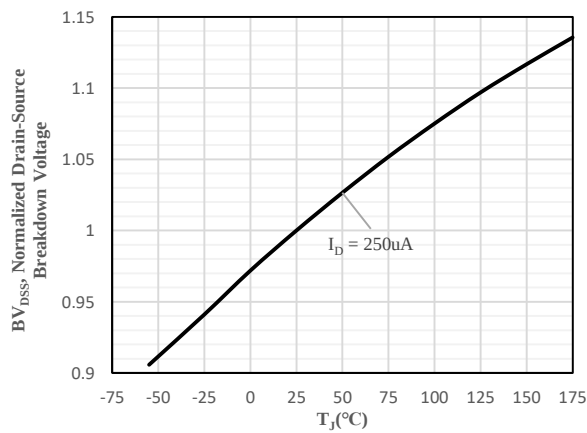


Fig 11 Normalized Breakdown Voltage vs. Junction Temperature

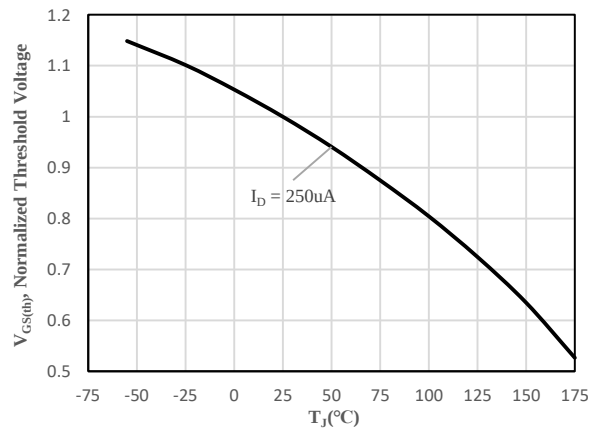


Fig 12 Normalized $V_{GS(th)}$ vs. Junction Temperature

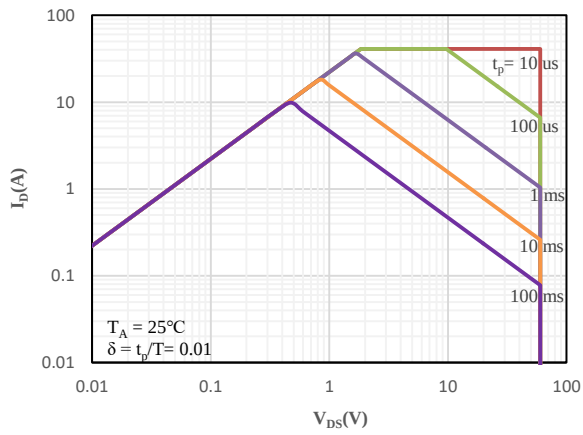


Fig 13 Safe Operation Area

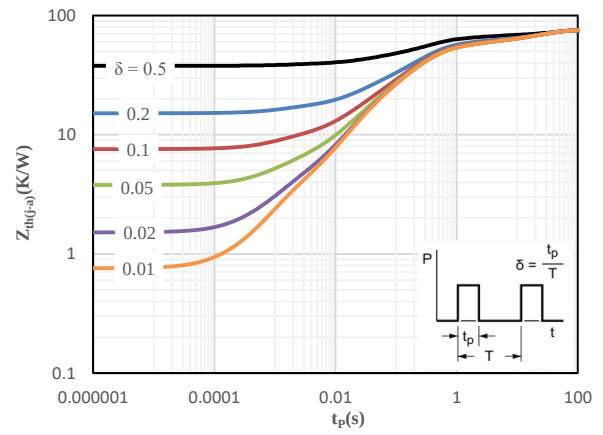
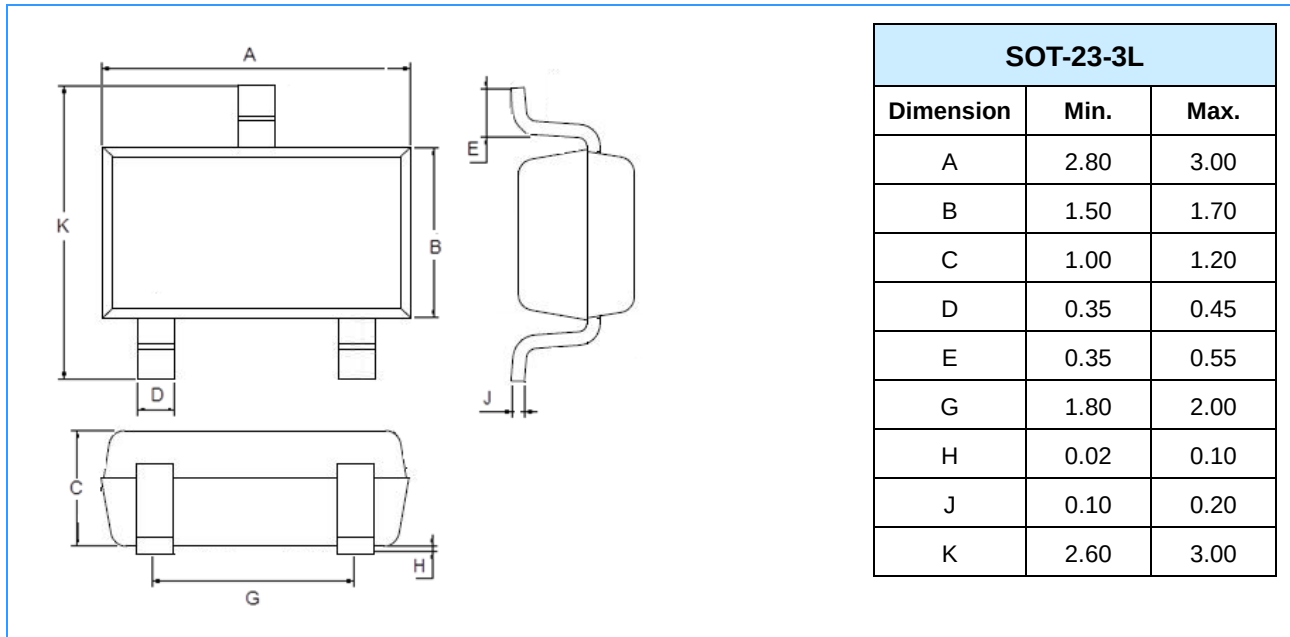
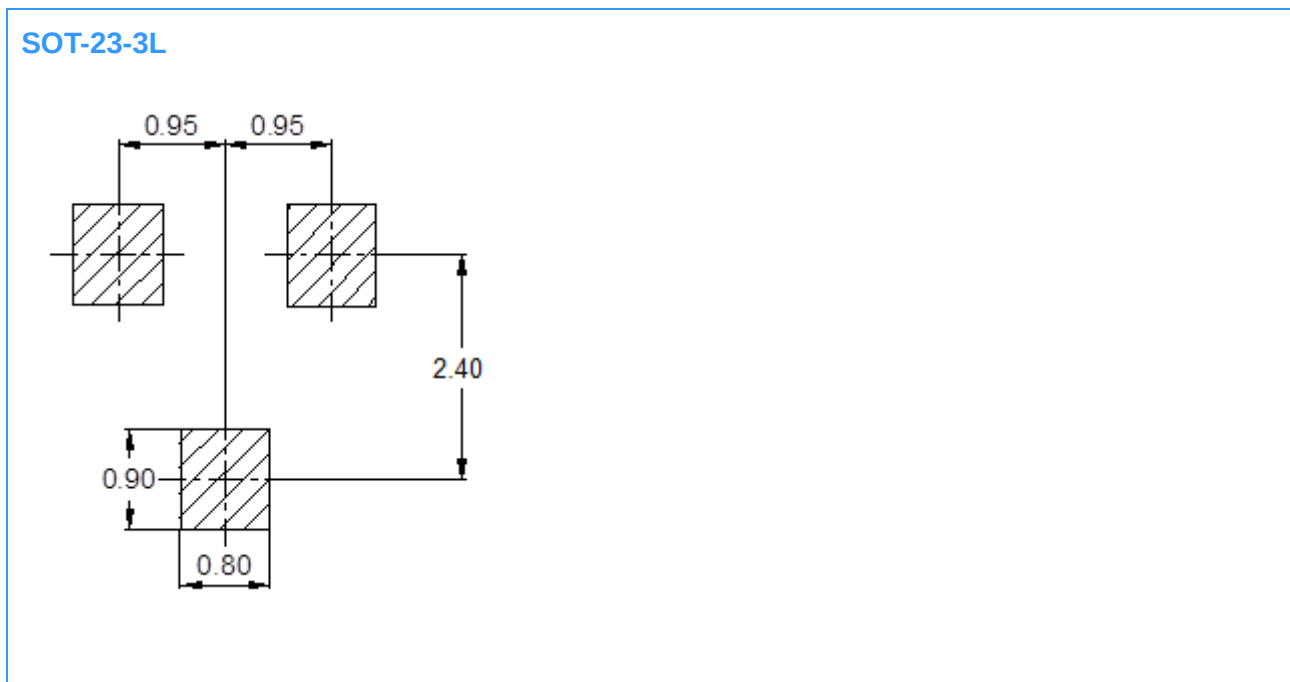


Fig 14 Maximum transient thermal impedance

Package Outline Dimensions (Unit: mm)



Mounting Pad Layout (Unit: mm)



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